Client Reference No. 068736.0231 PATENT

PTO-1449 Information Disclosure Citation In an Application	Application No. 10/678,837	Applicant(s): OLOF TORNBLAD ET AL.	
	Docket Number 068736.0231	Group Art Unit 2822	Filing Date October 3, 2003

U.S. PATENT DOCUMENTS

		DOCUMENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
	1	4,811,075	03/07/89	Eklund	357	46	04/24/87
	2	5,155,563	10/13/92	Davies et al.	357	23.4	03/18/91
	3	5,313,082	05/17/94	Eklund	257	262	02/16/93
	4	6,168,983	01/02/01	Rumennik et al.	438	188	02/05/99
	5	6,563,171	05/13/03	Disney	257	342	11/12/02

FOREIGN PATENT DOCUMENTS

		DOCUMENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES	TRANSLATION NO

NON-PATENT DOCUMENTS

		DOCUMENT (Including Author, Title, Source, and Pertinent Pages)	DATE
	6	J.A. Appels and H.M.J. Vaes, "High voltage thin layer devices (RESURF devices)", IEDM technical digest, pp. 238-241	1979
	7	H.M.J. Vaes and J.A. Appels, "High voltage high current lateral devices", IEDM technical digest, pp. 87-90	1980
	8	T. Fujihira, "Theory of Semiconductor Superjunction Devices", Jpn. J. Appl. Phys., vol. 36, pp. pp. 6254-6262	1997
	9	G. Deboy, M. Marz, J.-P. Stengl, H. Strack, J. Tihanyi and H. Weber, "A new generation of high voltage MOSFETs breaks the limit line of silicon", IEDM technical digest, pp. 683-685	1998
	10	A. Ludikhuize, "A review of RESURF technology", Proc. of ISPSD, p. 11	2000
	11	J. Cai, C. Ren, N. Balasubramanian and J.K.O. Sin, "A novel high performance stacked LDD RF LDMOSFET, IEEE Electron Device Lett., vol. 22, no. 5, pp. 236-238	2001
	12	J.G. Mena and C.A.T. Salama, "High voltage multiple-resistivity Drift-Region LDMOS", Solid State Electronics, Vol. 29, No. 6, pp. 647-656	1986
	13	M.D. Pocha and R.W. Dutton, "A computer-aided design model for High-Voltage Double Diffused MOS (DMOS) Transistors", IEEE Journal of Solid-State Circuits, Vol. SC-11, No. 5	1976
	14	I. Yoshia, M. Katsueda, S. Ohtaka, Y. Maruyama and T. Okabe; "High Efficient 1.5 GHz Si Power MOSFET for Digital Cellular Front End"; Proceedings of International Symposium on Power Semiconductor Devices & ICs; Tokyo, pp. 156-157	1992

EXAMINER	DATE CONSIDERED
John M. Howard	1-31-05

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.